



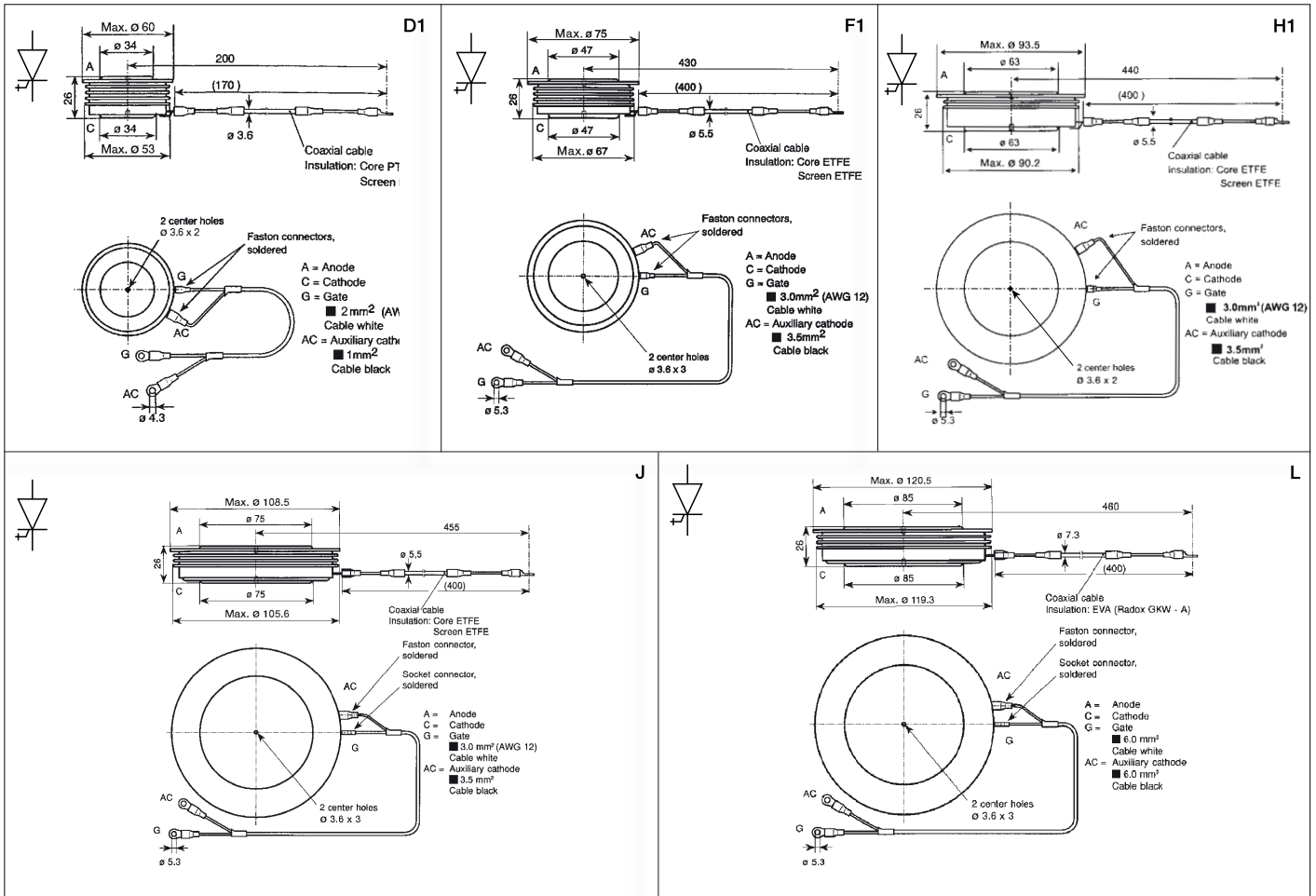
Asymmetric GTOs

Part number	V _{DRM}	V _{DC}	V _{RRM}	I _{TGQM} at C _S		I _{TAVM}	I _{TSM}	V _T	V _{T0}	r _T	T _{VJM}	R _{thJC}	R _{thCH}	F _m	Housing
	V	V	V	A	μF	T _c = 85°C	10ms	I _{TGQM}	T _{VJM}	mΩ	°C	K/kW	K/kW	kN	
						A	kA	V	V						
5SGA 15F2502	2500	1400	17	1500	3	570	10.0	2.80	1.45	0.90	125	27	8	15	F1
5SGA 20H2501	2500	1400	17	2000	4	830	16.0	2.80	1.66	0.57	125	17	5	20	H1
5SGA 25H2501	2500	1400	17	2500	6	830	16.0	3.10	1.66	0.57	125	17	5	20	H1
5SGA 30J2501	2500	1400	17	3000	5	1300	30.0	2.50	1.50	0.33	125	12	3	40	J
5SGA 06D4502	4500	2800	17	600	1	210	3.0	4.00	1.90	3.50	125	50	8	11	D1
5SGA 20H4502	4500	2200	17	2000	4	710	13.0	3.50	1.80	0.85	125	17	5	20	H1
5SGA 30J4502	4500	2800	17	3000	6	930	24.0	4.00	2.20	0.60	125	12	3	40	J
5SGA 40L4501	4500	2800	17	4000	6	1000	25.0	4.40	2.10	0.58	125	11	3	40	L

Asymmetric fine pattern GTOs with buffer layer

5SGF 30J4502	4500	3000	17	3000	3	960	24.0	3.90	1.80	0.70	125	12	3	33	J
5SGF 40L4502	4500	2800	17	4000	6	1180	25.0	3.80	1.20	0.65	125	11	3	40	L

Please refer to page 74 for part numbering structure.



Dimensions in mm

Fast recovery diode recommendation

For all GTO types, ABB offers matching free-wheeling and snubber diodes.

The actual choice of the diode depends on the specific application. Please see application note 5SYA 2064, Applying fast recovery diodes, on www.abb.com/semiconductors.